

HIGH EFFICIENCY ULTRAFAST DIODE

Table 1: Main Product Characteristics

$I_{F(AV)}$	1 A
V_{RRM}	200 V
$T_j (max)$	175°C
$V_F(max)$	0.78 V
$t_{rr} (max)$	20 ns

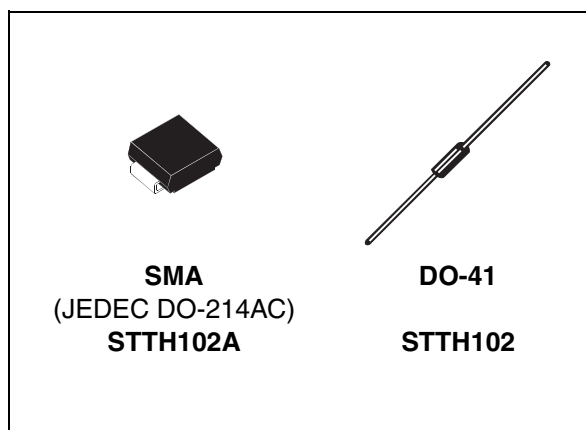
FEATURES AND BENEFITS

- Very low conduction losses
- Negligible switching losses
- Low forward and reverse recovery times
- High junction temperature

DESCRIPTION

The STTH102, which is using ST's new 200V planar technology, is specially suited for switching mode base drive and transistor circuits.

The device is also intended for use as a free wheeling diode in power supplies and other power switching applications.


Table 2: Order Codes

Part Number	Marking
STTH102A	U12
STTH102	STTH102
STTH102RL	STTH102

Table 3: Absolute Ratings (limiting values)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			200	V
I _{F(AV)}	Average forward current	SMA	T _L = 148°C δ = 0.5	1	A
		DO-41	T _L = 130°C δ = 0.5		
I _{FSM}	Surge non repetitive forward current	SMA	tp = 10 ms Sinusoidal	40	A
		DO-41		50	
T _{stg}	Storage temperature range			-65 to + 175	°C
T _j	Maximum operating junction temperature			175	°C
dV/dt	Critical rate of rise of reverse voltage			10000	V/μs

Table 4: Thermal Resistance

Symbol	Parameter		Value	Unit
$R_{th(j-l)}$	Junction to lead	Lead length = 10 mm	SMA	30
			DO-41	50

Table 5: Static Electrical Characteristics

Symbol	Parameter	Tests conditions		Min.	Typ	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			1	μA
		$T_j = 125^\circ\text{C}$			1	25	
V_F^{**}	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 700\text{ mA}$ (SMA)			0.90	V
			$I_F = 1\text{ A}$			0.97	
		$T_j = 125^\circ\text{C}$	$I_F = 1\text{ A}$		0.68	0.78	

Pulse test: * $t_p = 5\text{ ms}$, $\delta < 2\%$

** $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation: $P = 0.65 \times I_{F(AV)} + 0.130 I_F^2(\text{RMS})$

Figure 1: Average forward power dissipation versus average forward current (SMA)

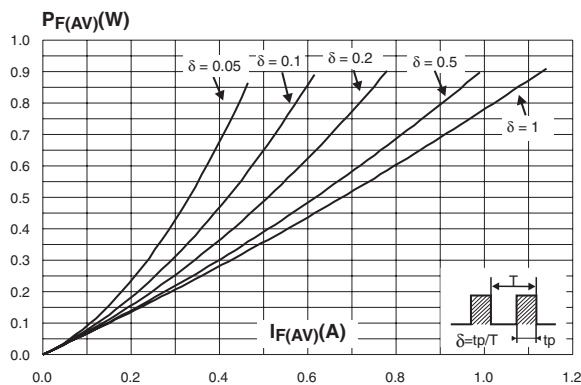


Figure 2: Average forward power dissipation versus average forward current (DO-41)

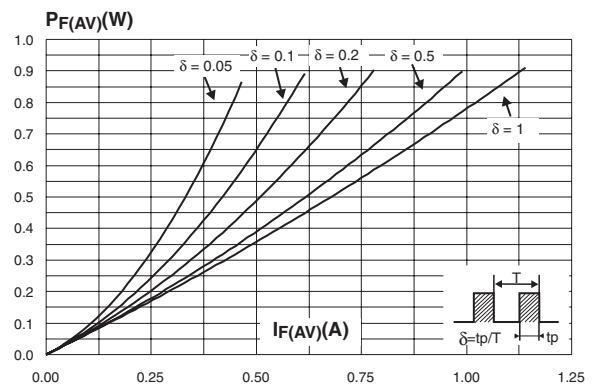
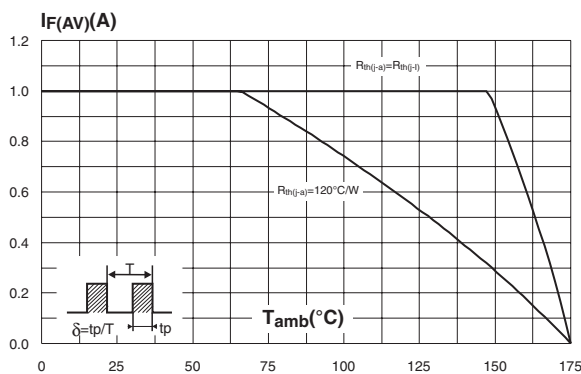
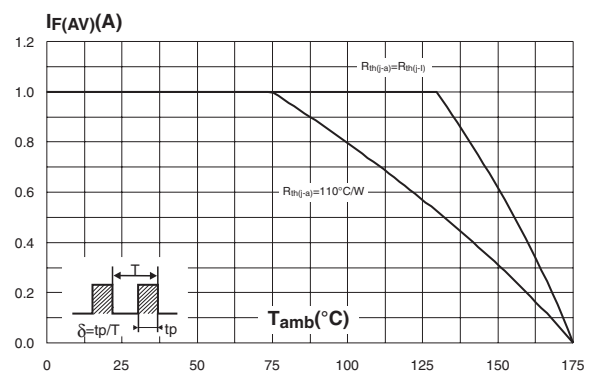
Figure 3: Average forward current versus ambient temperature ($\delta = 0.5$) (SMA)Figure 4: Average forward current versus ambient temperature ($\delta = 0.5$) (DO-41)

Figure 5: Relative variation of thermal impedance junction to ambient versus pulse duration (epoxy printed circuit board, $e(\text{Cu})=35\mu\text{m}$, recommended pad layout) (SMA)

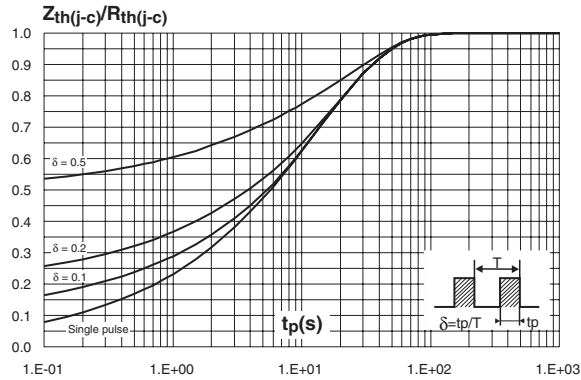


Figure 6: Relative variation of thermal impedance junction to ambient versus pulse duration (DO-41)

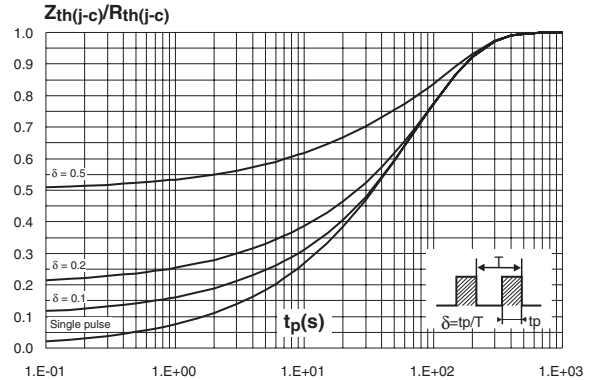


Figure 7: Forward voltage drop versus forward current

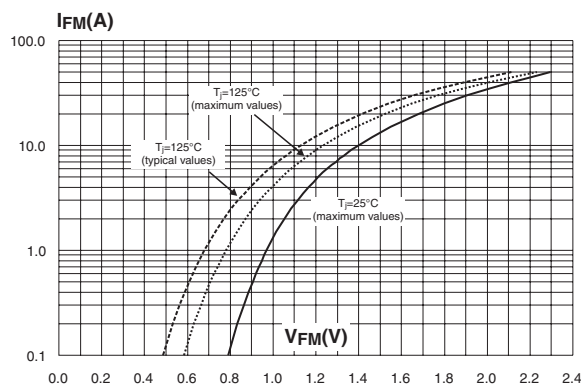


Figure 8: Junction capacitance versus reverse voltage applied (typical values)

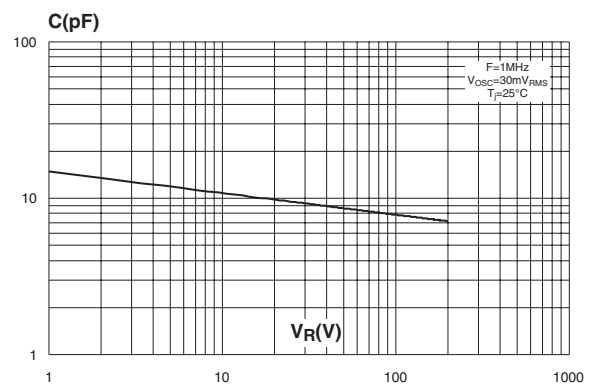


Figure 9: Reverse recovery time versus dI_F/dt (90% confidence)

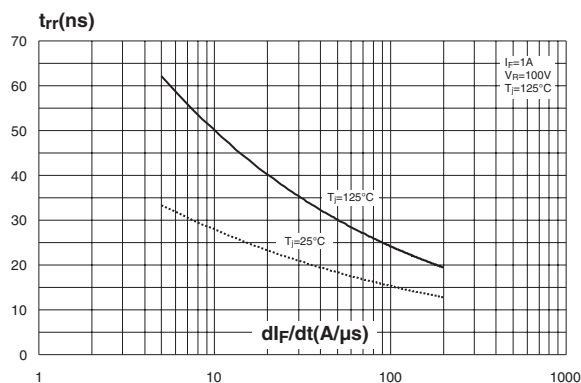


Figure 10: Peak recovery current versus dI_F/dt (90% confidence)

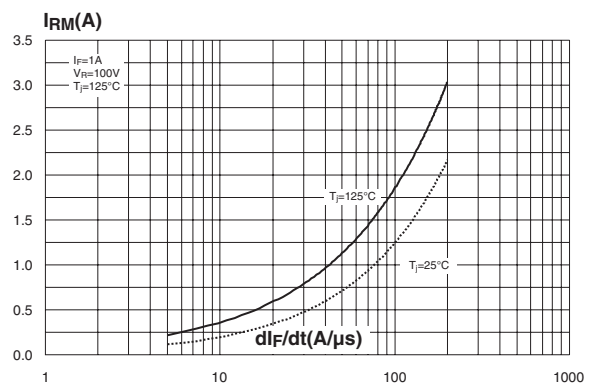


Figure 11: Reverse recovery charges versus di_F/dt (90% confidence)

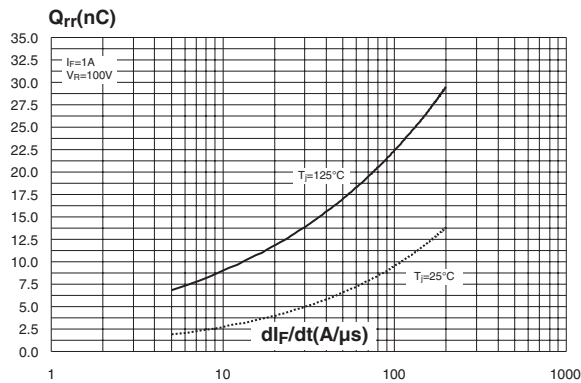


Figure 12: Relative variations of dynamic parameters versus junction temperature

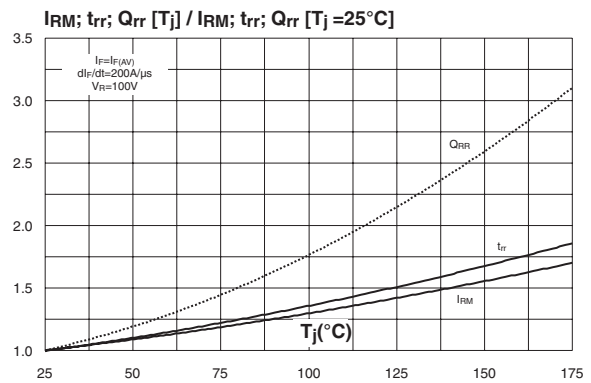


Figure 13: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board FR4, copper thickness: 35μm) (SMA)

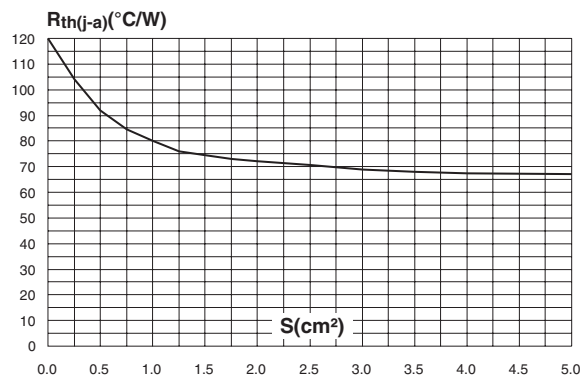


Figure 14: Thermal resistance versus lead length (DO-41)

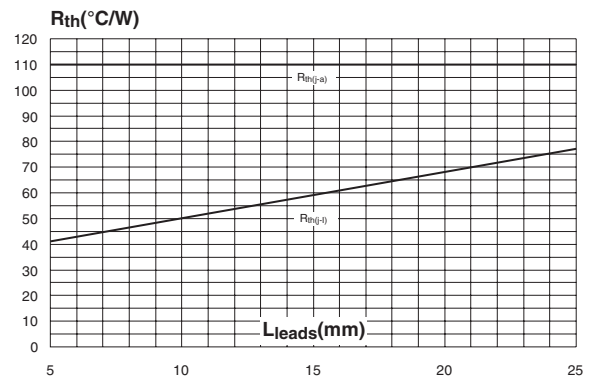


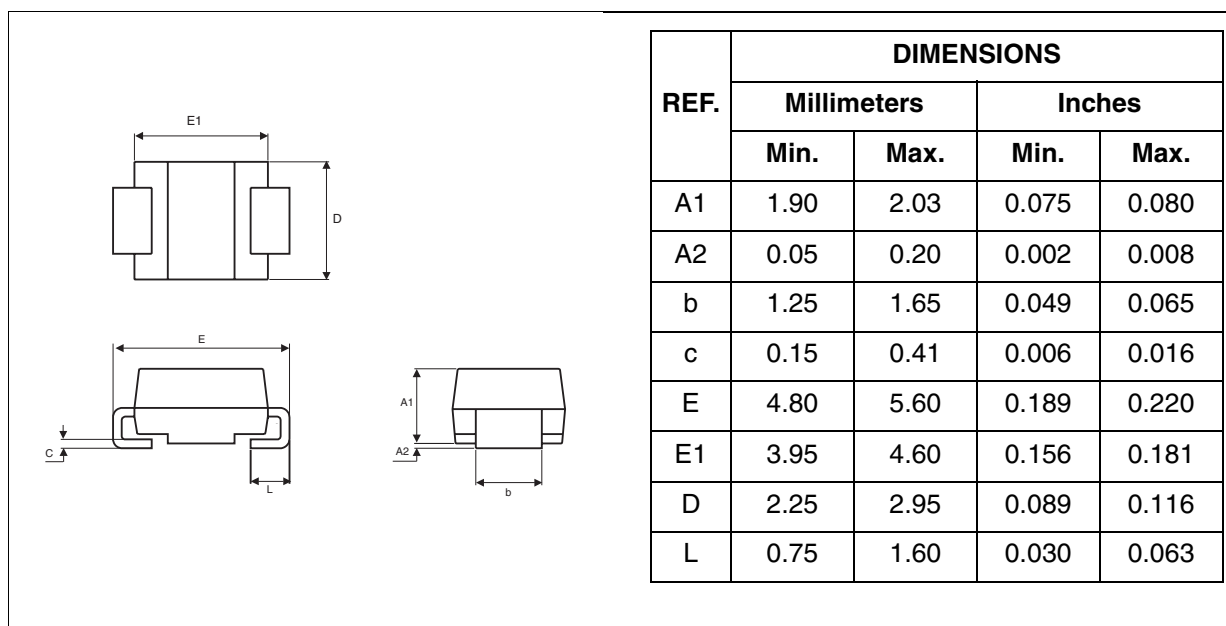
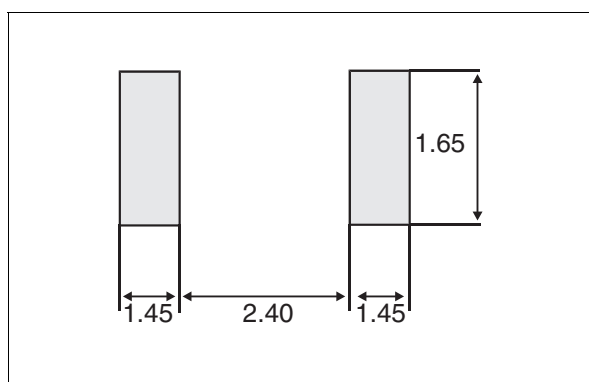
Figure 15: SMA Package Mechanical Data**Figure 16: SMA Foot Print Dimensions**
(in millimeters)

Figure 17: DO-41 Package Mechanical Data

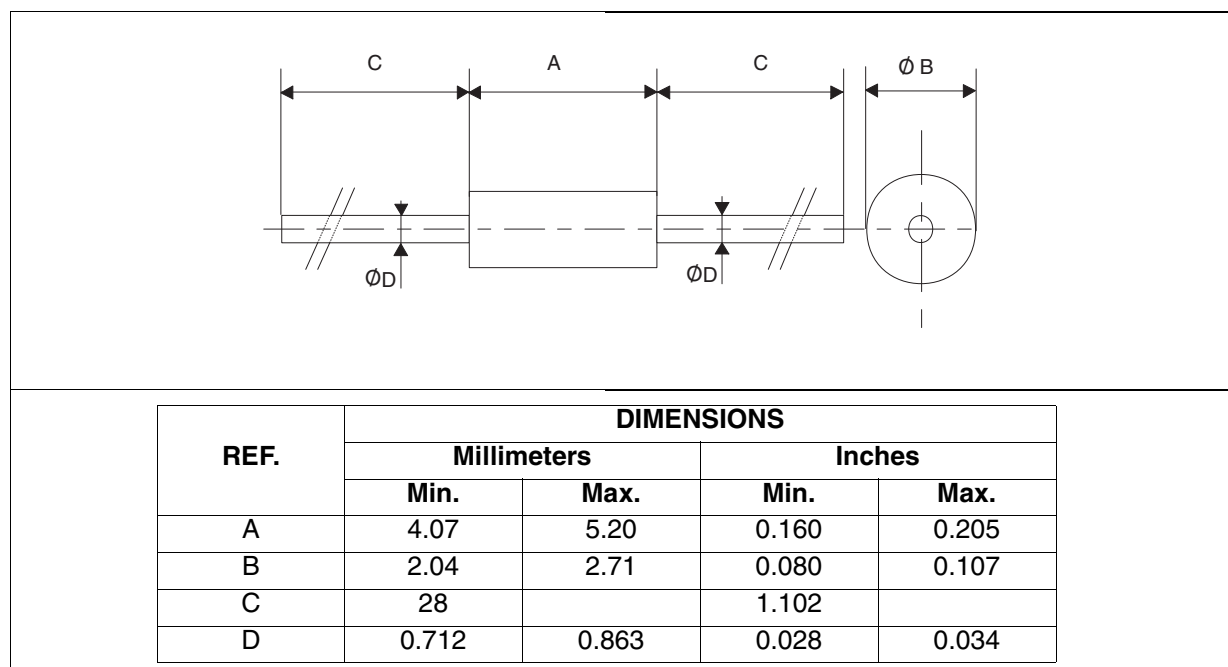


Table 6: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH102A	U12	SMA	0.068 g	5000	Tape & reel
STTH102	STTH102	DO-41	0.34 g	2000	Ammopack
STTH102RL	STTH102	DO-41	0.34 g	5000	Tape & reel

- Band indicates cathode
- Epoxy meets UL94, V0

Table 7: Revision History

Date	Revision	Description of Changes
Jul-2003	2A	Last update.
Aug-2004	3	1. SMA package dimensions update. Reference A1 max. changed from 2.70mm (0.106inc.) to 2.03mm (0.080). 2. SMA and DO-41 datasheets merged
27-Jun-2005	4	Corrected error in title.

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